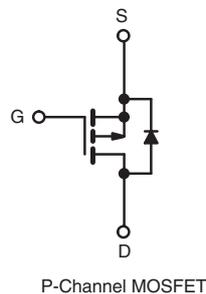
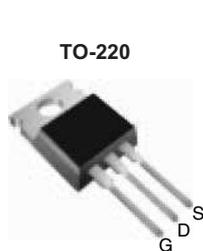


Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	- 100
$R_{DS(on)}$ (Ω)	$V_{GS} = -10$ V 0.30
Q_g (Max.) (nC)	38
Q_{gs} (nC)	6.8
Q_{gd} (nC)	21
Configuration	Single



FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- P-Channel
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available


RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION	
Package	TO-220
Lead (Pb)-free	IRF9530PbF
	SiHF9530-E3
SnPb	IRF9530
	SiHF9530

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 100	V	
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current	V_{GS} at - 10 V	I_D	$T_C = 25$ °C	- 12	A
			$T_C = 100$ °C	- 8.2	
Pulsed Drain Current ^a		I_{DM}	- 48		
Linear Derating Factor			0.59	W/°C	
Single Pulse Avalanche Energy ^b		E_{AS}	400	mJ	
Repetitive Avalanche Current ^a		I_{AR}	- 12	A	
Repetitive Avalanche Energy ^a		E_{AR}	8.8	mJ	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	88	W	
Peak Diode Recovery dV/dt ^c		dV/dt	- 5.5	V/ns	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d		
Mounting Torque	6-32 or M3 screw		10		lbf · in
			1.1	N · m	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = -25$ V, starting $T_J = 25$ °C, $L = 4.2$ mH, $R_G = 25$ Ω , $I_{AS} = -12$ A (see fig. 12).
- $I_{SD} \leq -12$ A, $dI/dt \leq 140$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
- 1.6 mm from case.

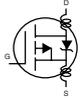
* Pb containing terminations are not RoHS compliant, exemptions may apply

IRF9530, SiHF9530

Vishay Siliconix



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-100	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$	-	-0.10	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-2.0	-	-4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$	-	-	-100	μA
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -7.2\text{ A}^b$	-	-	0.30	Ω
Forward Transconductance	g_{fs}	$V_{DS} = -50\text{ V}, I_D = -7.2\text{ A}^b$	3.7	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5	-	860	-	pF
Output Capacitance	C_{oss}		-	340	-	
Reverse Transfer Capacitance	C_{rss}		-	93	-	
Total Gate Charge	Q_g	$V_{GS} = -10\text{ V}, I_D = -12\text{ A}, V_{DS} = -80\text{ V}$, see fig. 6 and 13 ^b	-	-	38	nC
Gate-Source Charge	Q_{gs}		-	-	6.8	
Gate-Drain Charge	Q_{gd}		-	-	21	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, I_D = -12\text{ A}, R_G = 12\text{ }\Omega, R_D = 3.9\text{ }\Omega$, see fig. 10 ^b	-	12	-	ns
Rise Time	t_r		-	52	-	
Turn-Off Delay Time	$t_{d(off)}$		-	31	-	
Fall Time	t_f		-	39	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p-n junction diode 	-	-	-12	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	-48	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = -12\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	-6.3	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = -12\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$	-	120	240	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.46	0.92	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

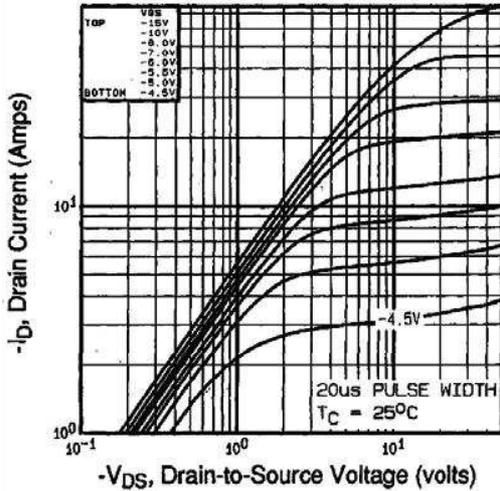


Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

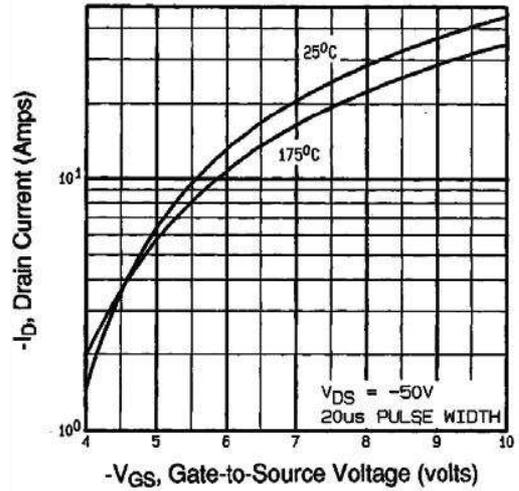


Fig. 3 - Typical Transfer Characteristics

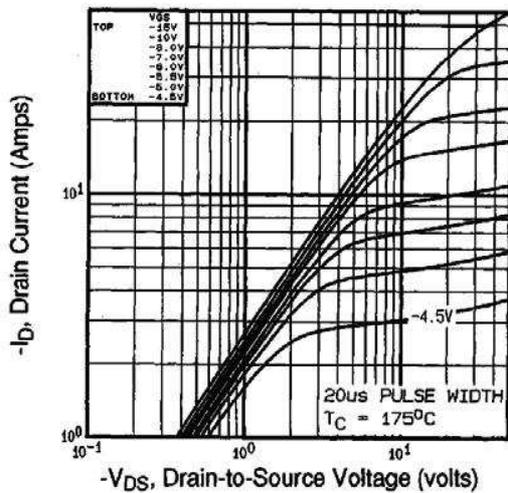


Fig. 2 - Typical Output Characteristics, $T_C = 175^\circ\text{C}$

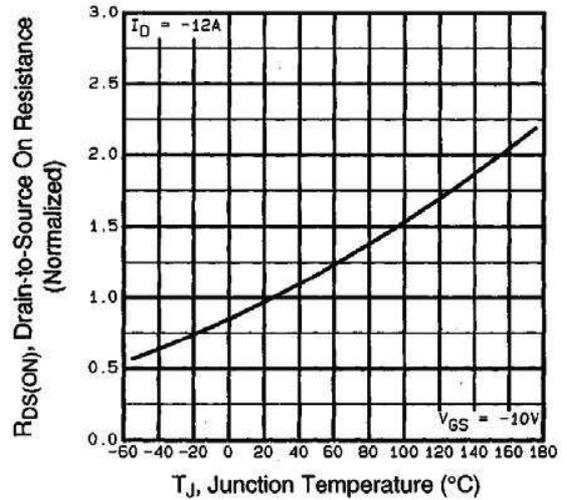


Fig. 4 - Normalized On-Resistance vs. Temperature

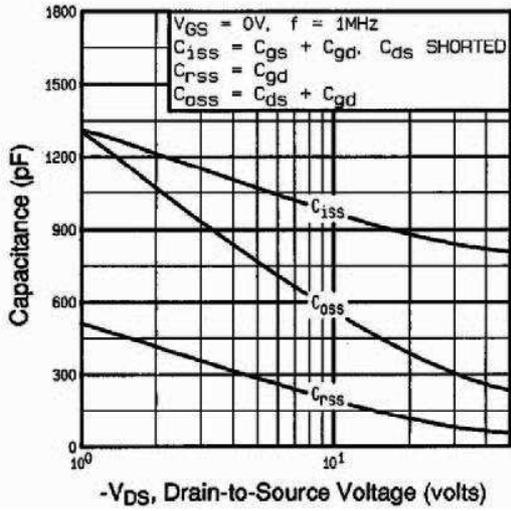


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

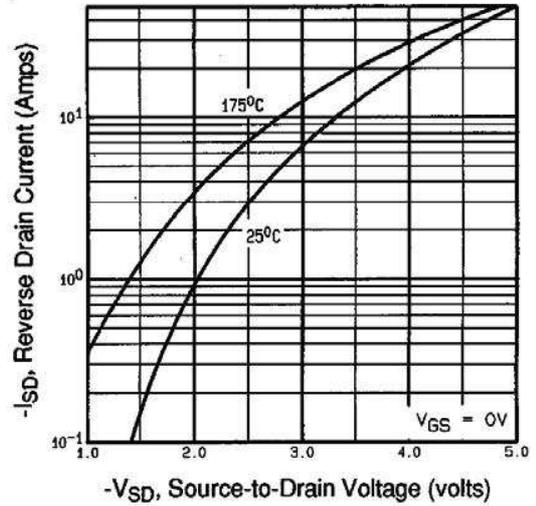


Fig. 7 - Typical Source-Drain Diode Forward Voltage

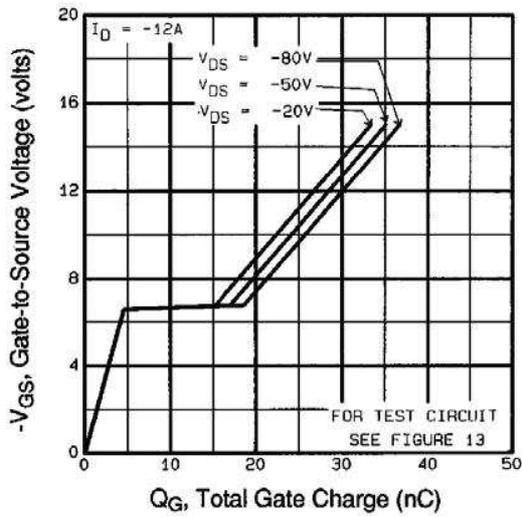


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

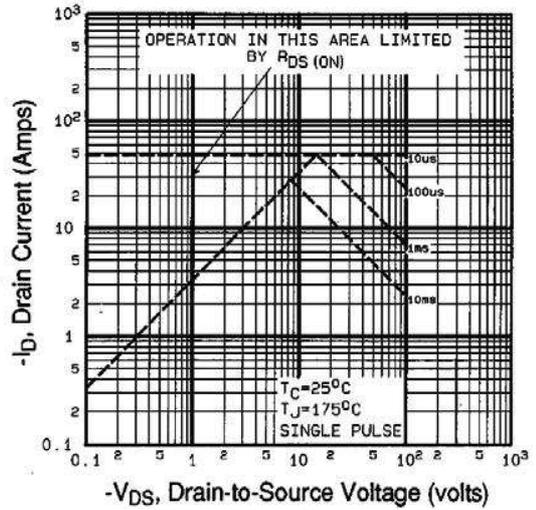


Fig. 8 - Maximum Safe Operating Area

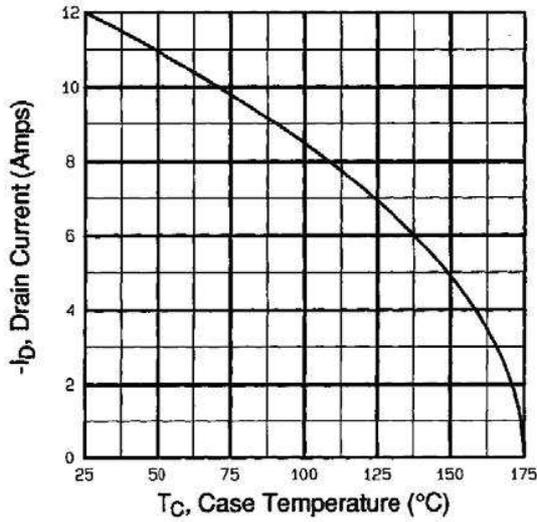


Fig. 9 - Maximum Drain Current vs. Case Temperature

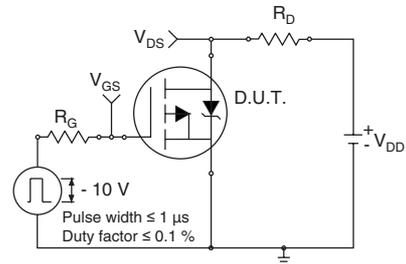


Fig. 10a - Switching Time Test Circuit

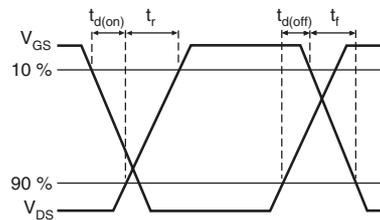


Fig. 10b - Switching Time Waveforms

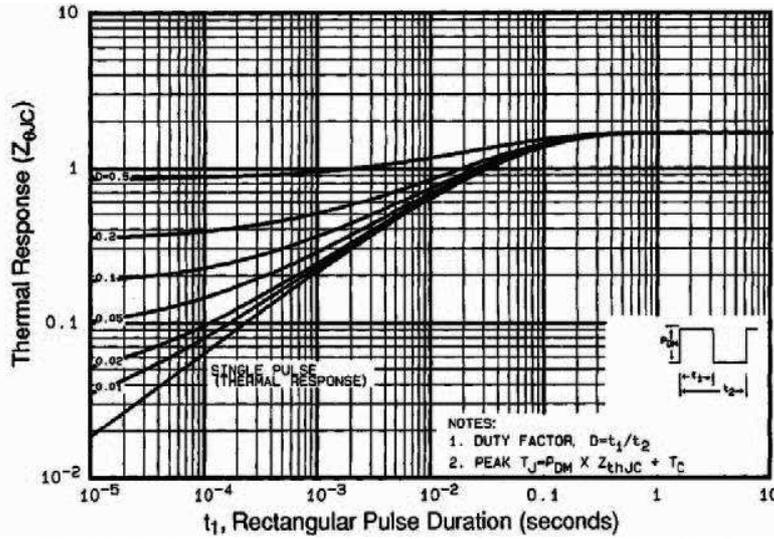


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

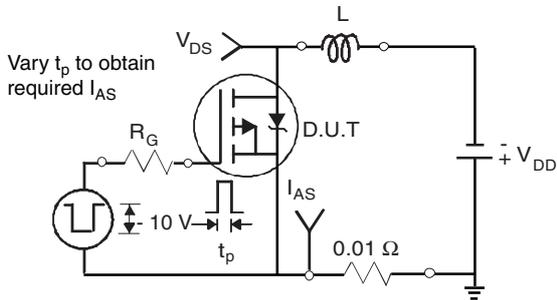


Fig. 12a - Unclamped Inductive Test Circuit

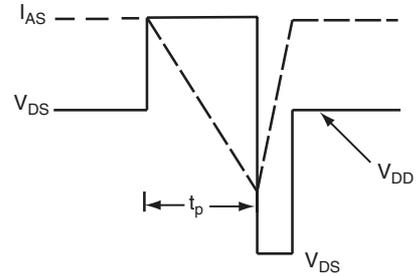


Fig. 12b - Unclamped Inductive Waveforms

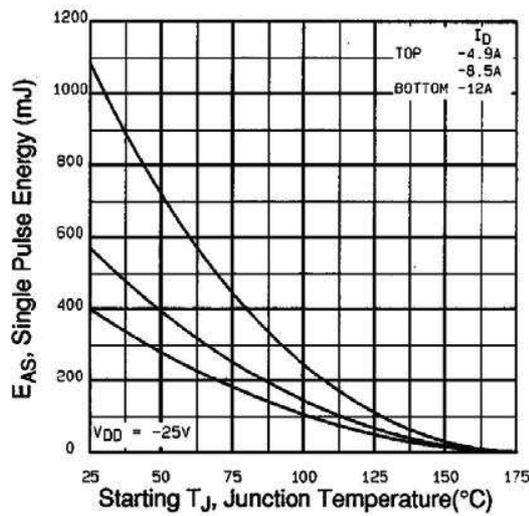


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

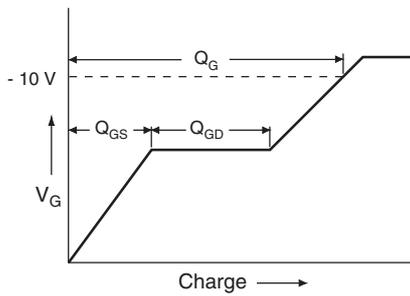


Fig. 13a - Basic Gate Charge Waveform

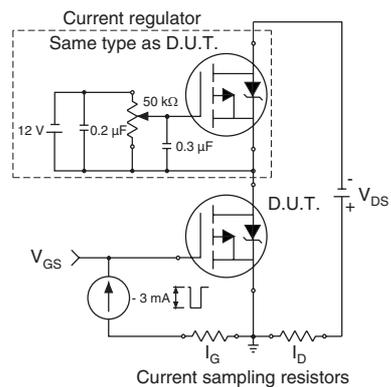
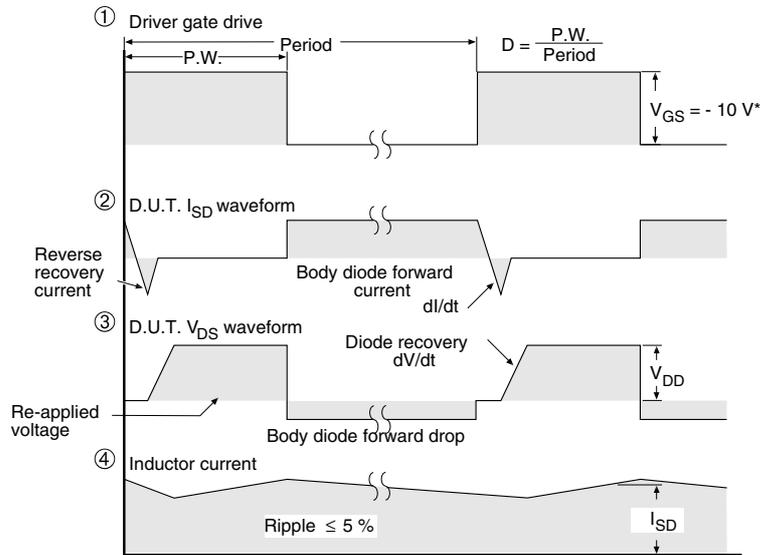
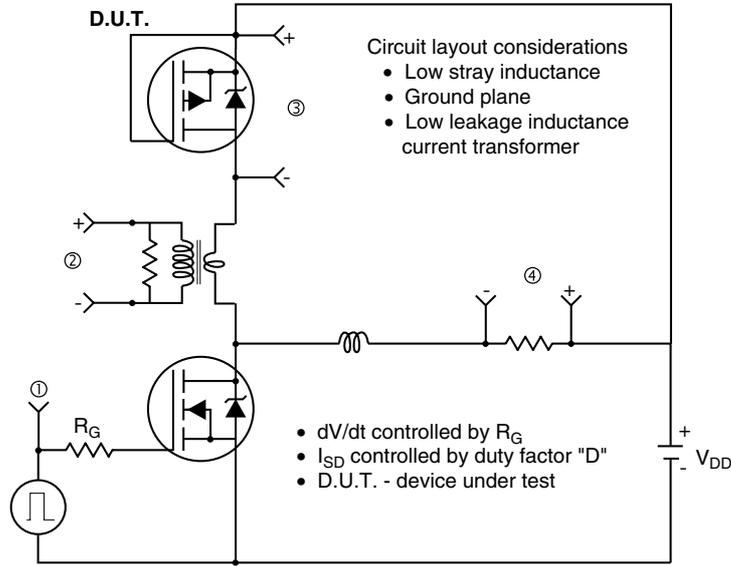


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = -5V$ for logic level and $-3V$ drive devices

Fig. 14 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?91076>.